DUAL N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

NEW PRODUCT

Features

- Dual N-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage (1.0V max)
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Small Surface Mount Package
- **Lead Free By Design/RoHS Compliant (Note 2)**
- **ESD Protected up to 2kV**
- **"Green" Device (Note 4)**
- **Qualified to AEC-Q101 standards for High Reliability**

Mechanical Data

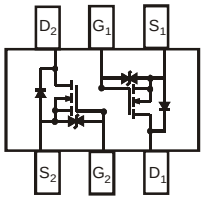
- Case: SOT-26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.015 grams (approximate)

ESD protected up 2kV

SOT-26

TOP VIEW

BOTTOM VIEW



TOP VIEW
Internal Schematic

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Drain Source Voltage		V_{DSS}	50	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current (Note 1)	Continuous Pulsed (Note 3)	I_D	305 800	mA

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	P_D	400	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	313	°C/W
Operating and Storage Temperature Range	T_j, T_{STG}	-65 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)							
Drain-Source Breakdown Voltage		BV_{DSS}	50	—	—	V	V_{GS} = 0V, I_D = 10μA
Zero Gate Voltage Drain Current	@ T_C = 25°C	I_{DSS}	—	—	60	nA	V_{DS} = 50V, V_{GS} = 0V
Gate-Body Leakage		I_{GSS}	—	—	1 500 50	μA nA nA	V_{GS} = ±12V, V_{DS} = 0V V_{GS} = ±10V, V_{DS} = 0V V_{GS} = ±5V, V_{DS} = 0V
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage		$V_{GS(th)}$	0.49	—	1.0	V	V_{DS} = V_{GS}, I_D = 250μA
Static Drain-Source On-Resistance		$R_{DS\ (ON)}$	— — —	— — —	3.0 2.5 2.0	Ω	V_{GS} = 1.8V, I_D = 50mA V_{GS} = 2.5V, I_D = 50mA V_{GS} = 5.0V, I_D = 50mA
On-State Drain Current		$I_{D(ON)}$	0.5	1.4	—	A	V_{GS} = 10V, V_{DS} = 7.5V
Forward Transconductance		$\|Y_{fs}\|$	200	—	—	mS	V_{DS} =10V, I_D = 0.2A
Source-Drain Diode Forward Voltage		V_{SD}	0.5	—	1.4	V	V_{GS} = 0V, I_S = 115mA
DYNAMIC CHARACTERISTICS							
Input Capacitance		C_{iss}	—	—	50	pF	V_{DS} = 25V, V_{GS} = 0V f = 1.0MHz
Output Capacitance		C_{oss}	—	—	25	pF	
Reverse Transfer Capacitance		C_{rss}	—	—	5.0	pF	

Notes:
1. Device mounted on FR-4 PCB.
2. No purposefully added lead.
3. Pulse width ≤10μS, Duty Cycle ≤1%.
4. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
5. Short duration pulse test used to minimize self-heating effect.

NEW PRODUCT

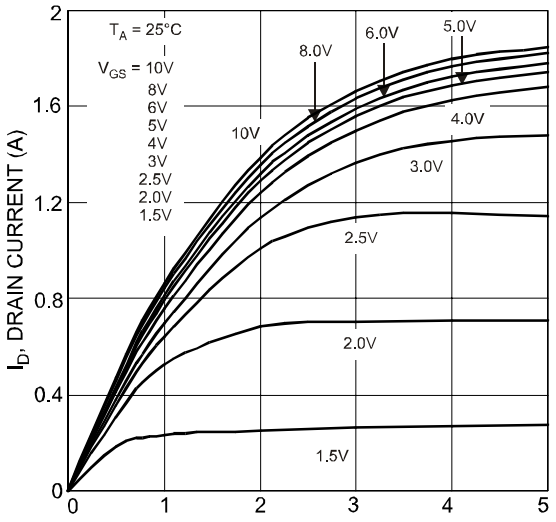


Fig. 1 Typical Output Characteristics

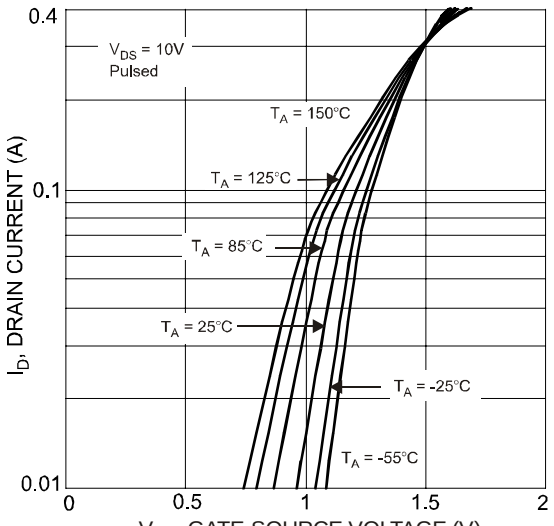


Fig. 2 Typical Transfer Characteristics

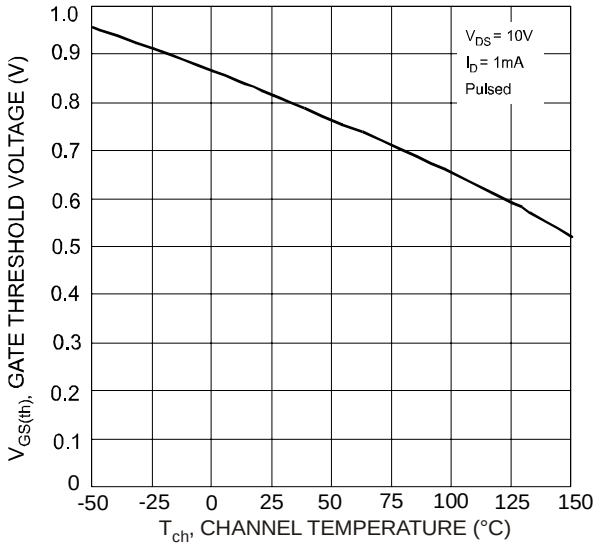


Fig. 3 Gate Threshold Voltage vs. Channel Temperature

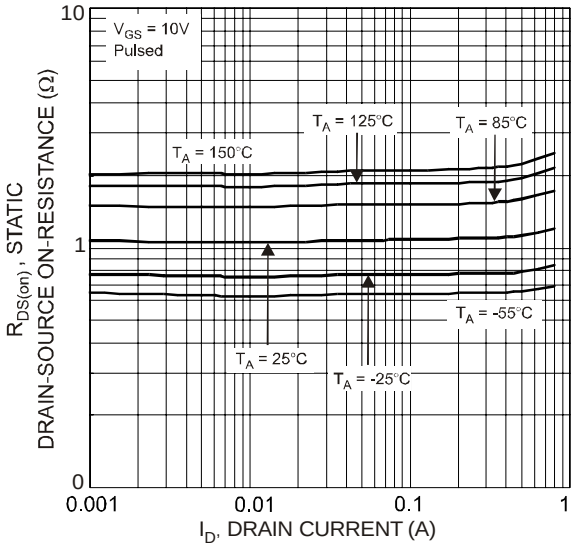


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

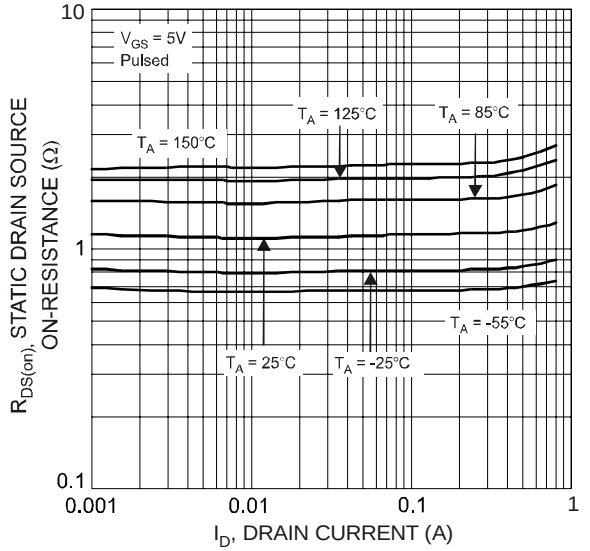


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

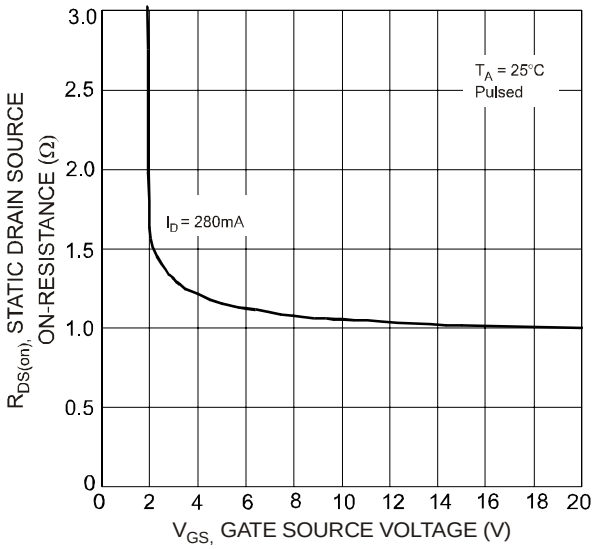


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage

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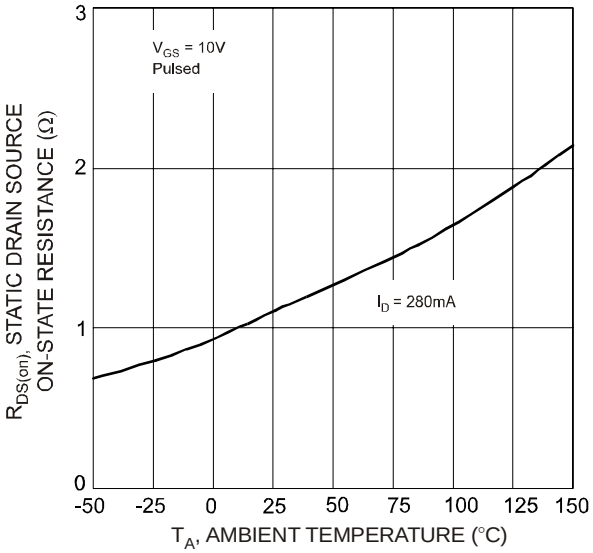


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

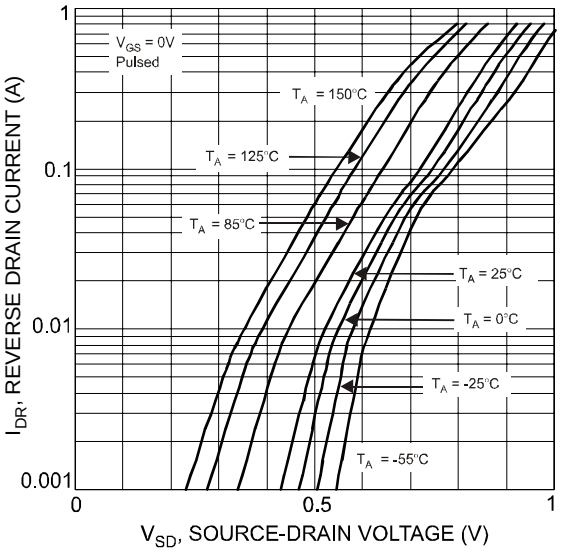


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

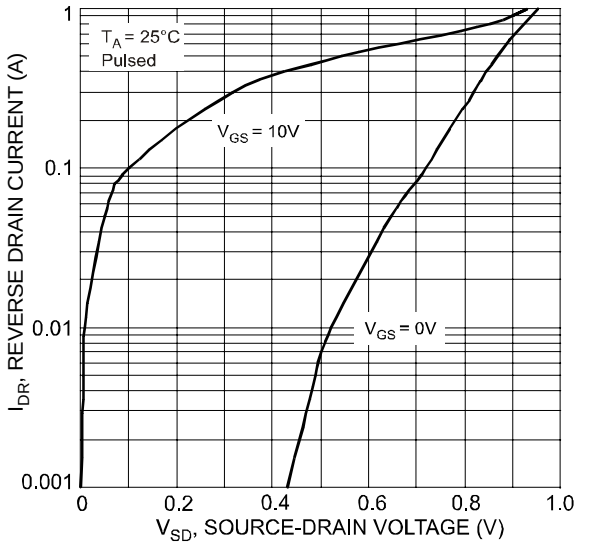


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage

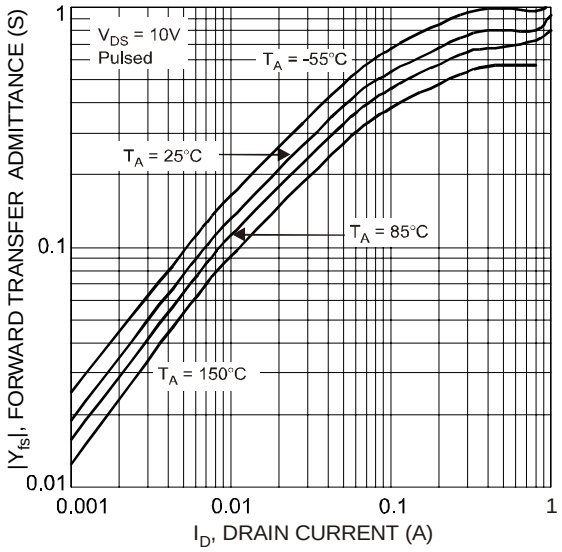


Fig.10 Forward Transfer Admittance vs. Drain Current

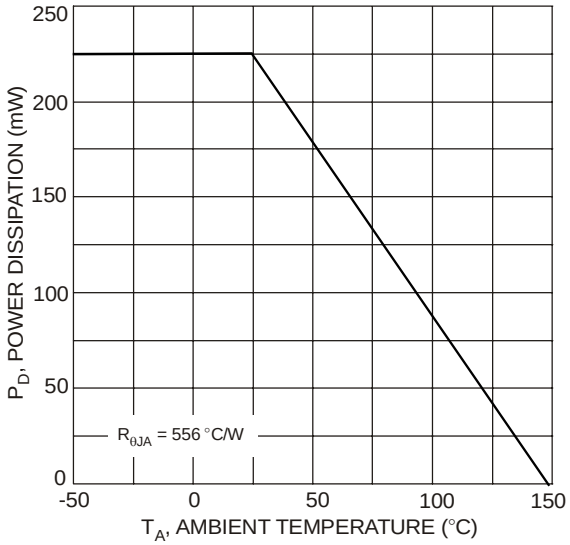


Fig. 11 Derating Curve - Total

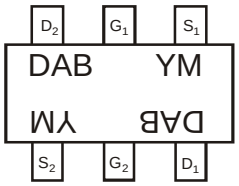
NEW PRODUCT

Ordering Information (Note 6)

Part Number	Case	Packaging
DMN5L06DMK-7	SOT-26	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



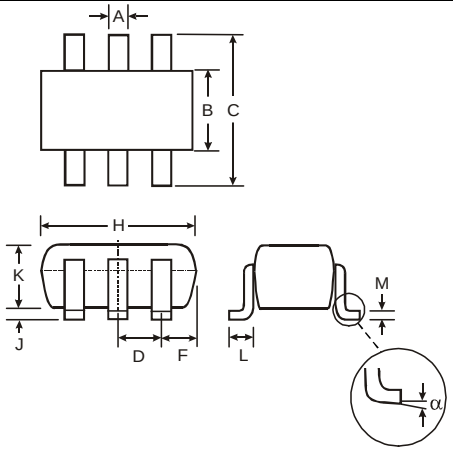
DAB = Marking Code
YM = Date Code Marking
Y = Year ex: T = 2006
M = Month ex: 9 = September

Date Code Key

Year	2006	2007	2008	2009	2010	2011	2012
Code	T	U	V	W	X	Y	Z

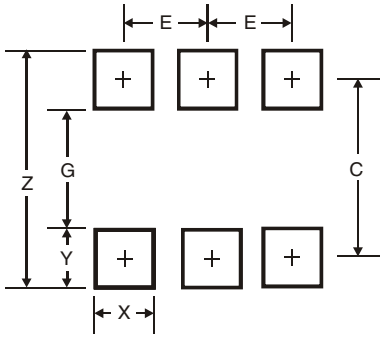
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Package Outline Dimensions



SOT-26			
Dim	Min	Max	Typ
A	0.35	0.50	0.38
B	1.50	1.70	1.60
C	2.70	3.00	2.80
D	–	–	0.95
F	–	–	0.55
H	2.90	3.10	3.00
J	0.013	0.10	0.05
K	1.00	1.30	1.10
L	0.35	0.55	0.40
M	0.10	0.20	0.15
α	0°	8°	–
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.20
G	1.60
X	0.55
Y	0.80
C	2.40
E	0.95

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